74HC125; 74HCT125

Quad buffer/line driver; 3-state

Rev. 5 — 19 January 2015 Product data sheet

1. General description

The 74HC125; 74HCT125 is a quad buffer/line driver with 3-state outputs controlled by the output enable inputs (nOE). A HIGH on nOE causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Complies with JEDEC standard no. 7A
- Input levels:
  - The 74HC125: CMOS levels
  - The 74HCT125: TTL levels
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC125N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HCT125N				
74HC125D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74HCT125D				
74HC125DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74HCT125DB				
74HC125PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74HCT125PW				

4. Functional diagram

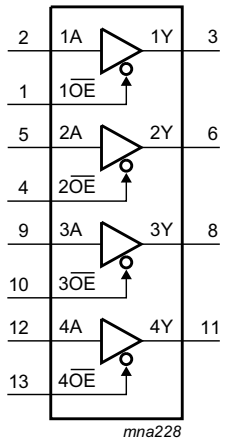


Fig 1. Logic symbol

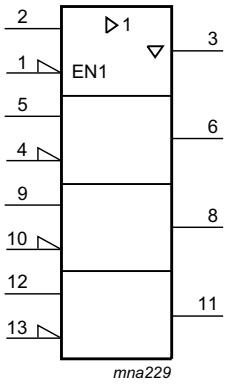


Fig 2. IEC logic symbol

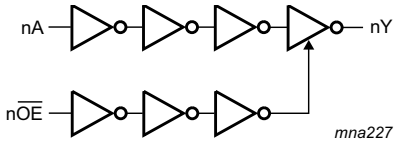


Fig 3. Logic diagram (one buffer)

5. Pinning information

5.1 Pinning

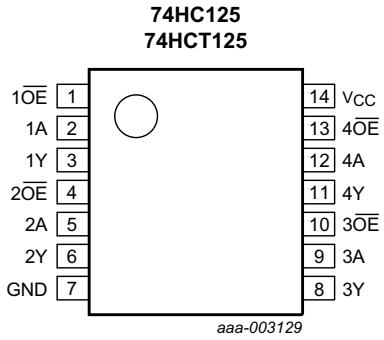


Fig 4. Pin configuration DIP14, SO14 and (T)SSOP14

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5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$1\overline{OE}$, $2\overline{OE}$, $3\overline{OE}$, $4\overline{OE}$	1, 4, 10, 13	output enable input (active LOW)
1A, 2A, 3A, 4A	2, 5, 9, 12	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V_{CC}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Control	Input	Output
$n\overline{OE}$	**nA**	**nY**
L	L	L
	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		−0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V [1]	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V [1]	-	±20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	-	±35	mA
I_{CC}	supply current		-	+70	mA
I_{GND}	ground current		-	−70	mA
T_{stg}	storage temperature		−65	+150	°C
P_{tot}	total power dissipation	[2]			
	DIP14 package		-	750	mW
	SO14 and (T)SSOP14 packages		-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP14 package: P_{tot} derates linearly with 12 mW/K above 70 °C.
For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
For (T)SSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC125			74HCT125			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC125										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.5	-	±5.0	-	±10.0	μA

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Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	-	80	-	160	μA
C_I	input capacitance		-	3.5	-					pF
74HCT125										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 4.5$ V								
		$I_O = -20$ μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -6$ mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 4.5$ V								
		$I_O = 20$ μA	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0$ mA	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1$ V; $I_O = 0$ A; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V	-	100	360	-	450	-	490	μA
C_I	input capacitance		-	3.5	-					pF

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10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC125										
t_{pd}	propagation delay	nA to nY; see Figure 5 [1]								
		V_{CC} = 2.0 V	-	30	100	-	125	-	150	ns
		V_{CC} = 4.5 V	-	11	20	-	25	-	30	ns
		V_{CC} = 5 V; C_L = 15 pF	-	9	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	9	17	-	21	-	26	ns
t_{en}	enable time	$n\overline{OE}$ to nY; see Figure 6 [2]								
		V_{CC} = 2.0 V	-	41	125	-	155	-	190	ns
		V_{CC} = 4.5 V	-	15	25	-	31	-	38	ns
		V_{CC} = 6.0 V	-	12	21	-	26	-	32	ns
t_{dis}	disable time	$n\overline{OE}$ to nY; see Figure 6 [3]								
		V_{CC} = 2.0 V	-	41	125	-	155	-	190	ns
		V_{CC} = 4.5 V	-	15	25	-	31	-	38	ns
		V_{CC} = 6.0 V	-	12	21	-	26	-	32	ns
t_t	transition time	nY; see Figure 5 [4]								
		V_{CC} = 2.0 V	-	14	60	-	75	-	90	ns
		V_{CC} = 4.5 V	-	5	12	-	15	-	18	ns
		V_{CC} = 6.0 V	-	4	10	-	13	-	15	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC} [5]	-	22	-	-	-	-	-	pF

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Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT125										
t_{pd}	propagation delay	nA to nY; see Figure 5 [1]								
		V_{CC} = 4.5 V	-	15	25	-	31	-	38	ns
		V_{CC} = 5 V; C_L = 15 pF	-	12	-	-	-	-	-	ns
t_{en}	enable time	$n\overline{OE}$ to nY; see Figure 6 [2]								
		V_{CC} = 4.5 V	-	15	28	-	35	-	42	ns
t_{dis}	disable time	$n\overline{OE}$ to nY; see Figure 6 [3]								
		V_{CC} = 4.5 V	-	15	25	-	31	-	38	ns
t_t	transition time	nY; see Figure 5 [4]	-	5	12	-	15	-	18	ns
C_{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V_I = GND to V_{CC} − 1.5 V [5]	-	24	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

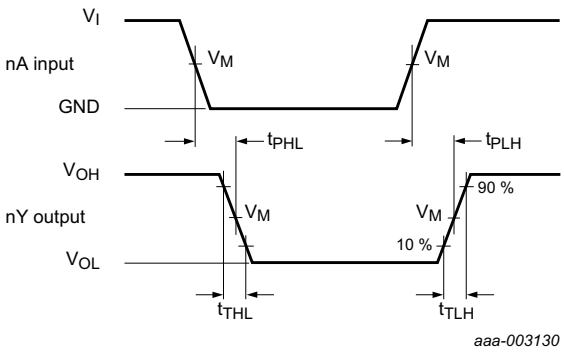
[2] t_{en} is the same as t_{PZH} and t_{PZL}.

[3] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[4] t_t is the same as t_{THL} and t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



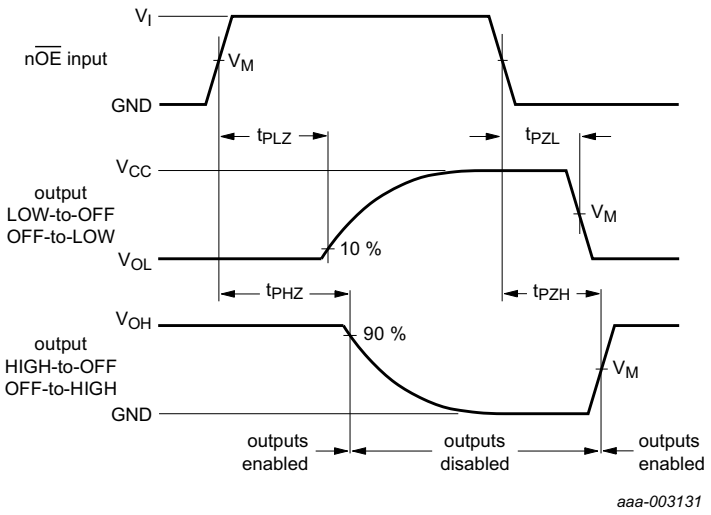
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (nA) to output (nY)

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Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

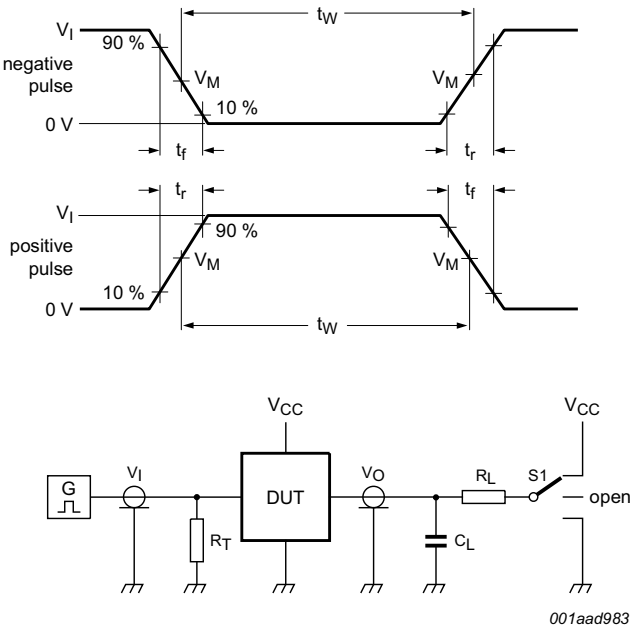
Fig 6. Enable and disable times

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC125	$0.5V_{CC}$	$0.5V_{CC}$
74HCT125	1.3 V	1.3 V

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Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Load circuit for switching times

Table 9. Test data

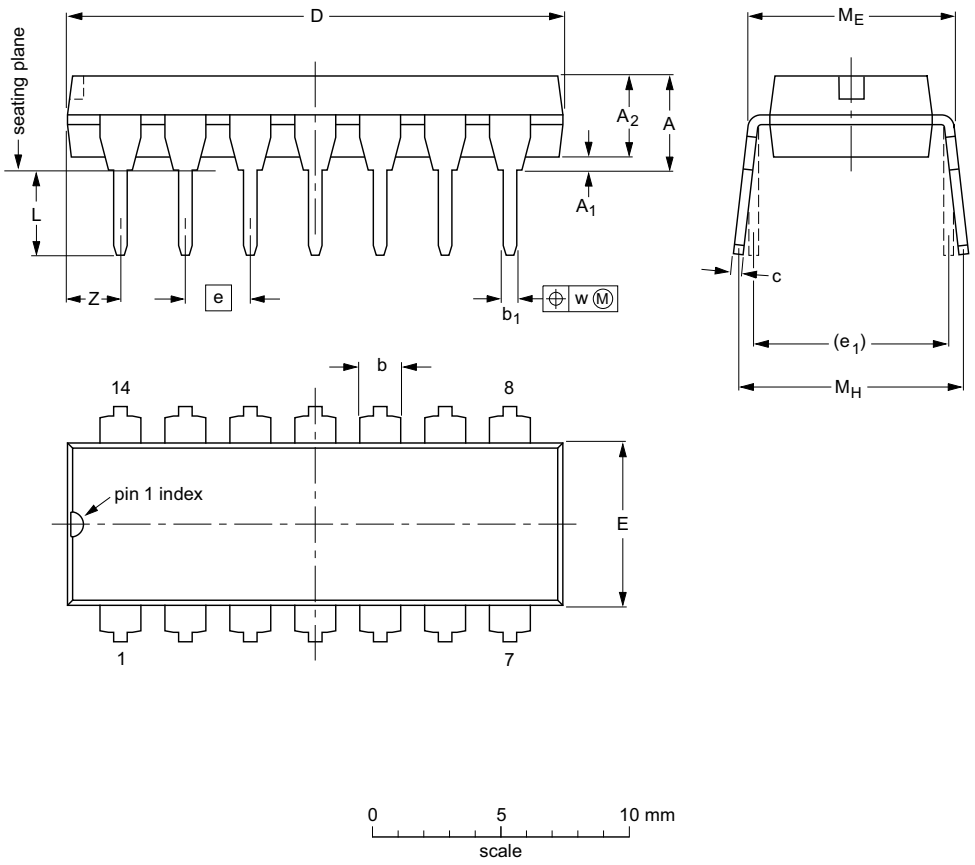
Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC125	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74HCT125	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

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12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil) **SOT27-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

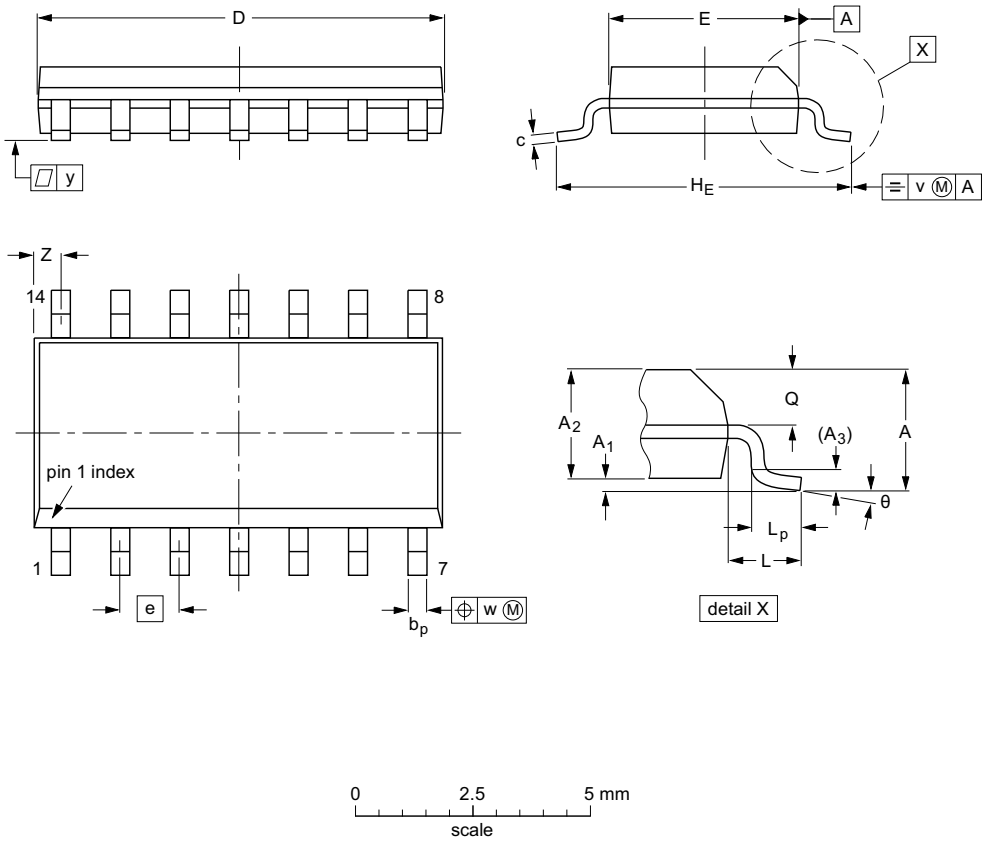
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT27-1	050G04	MO-001	SC-501-14			~~99-12-27~~ 03-02-13

Fig 8. Package outline SOT27-1 (DIP14)

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SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

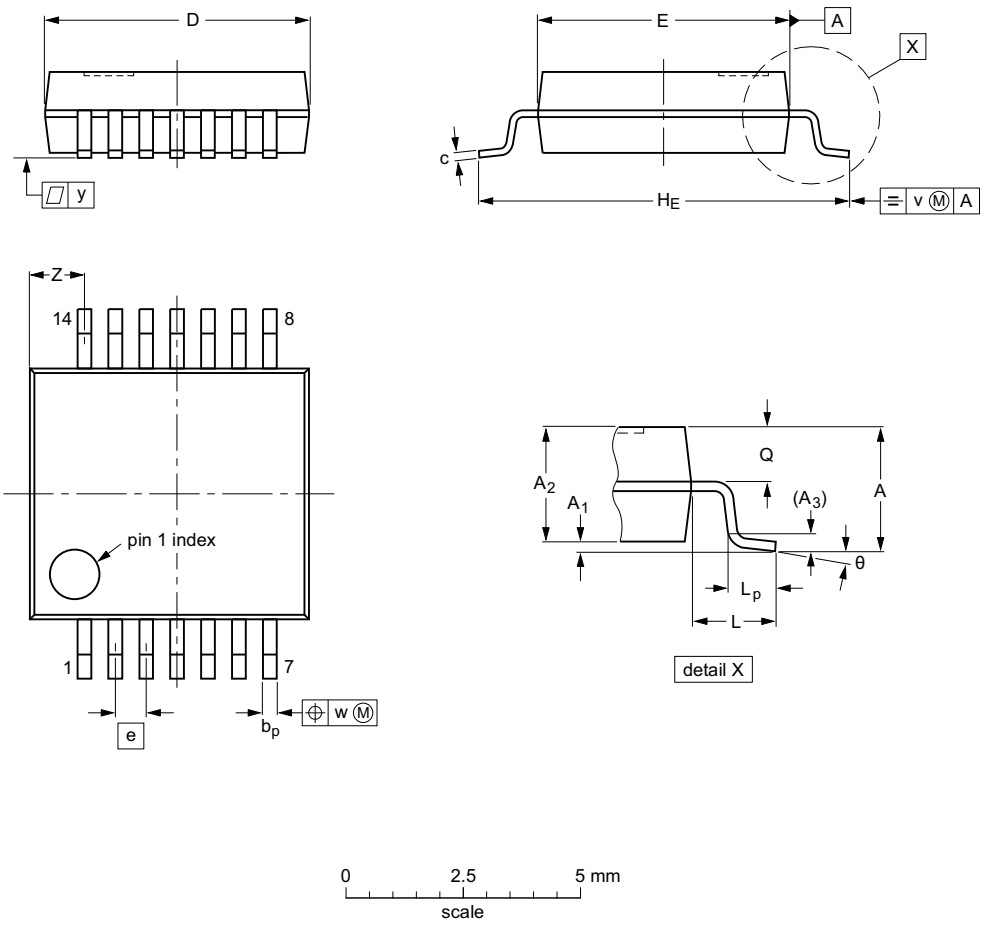
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	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT108-1 (SO14)

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm **SOT337-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8^o 0^o

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

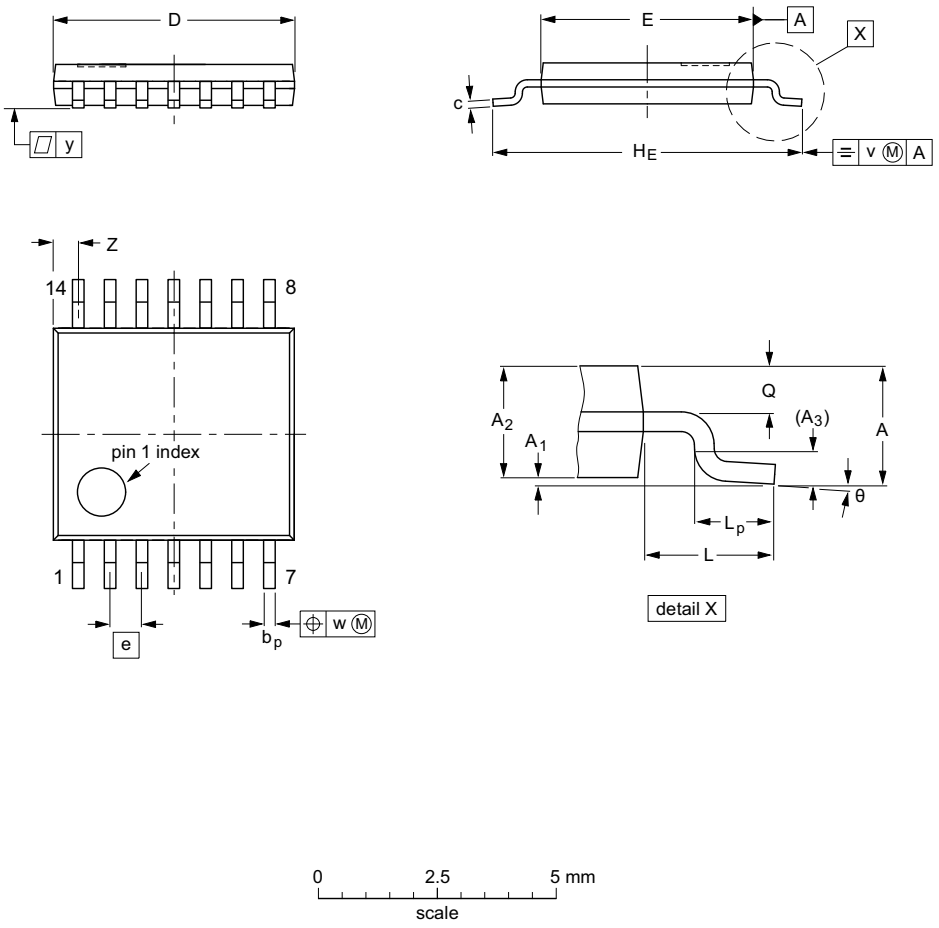
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT337-1		MO-150				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT337-1 (SSOP14)

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm **SOT402-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT402-1		MO-153				~~99-12-27~~ 03-02-18

Fig 11. Package outline SOT402-1 (TSSOP14)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
LSTTL	Low-power Schottky Transistor-Transistor Logic
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
CDM	Charge-Device Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT125 v.5	20150119	Product data sheet	-	74HC_HCT125 v.4
Modifications:	• Table 7: Power dissipation capacitance condition for 74HCT125 is corrected.			
74HC_HCT125 v.4	20130110	Product data sheet	-	74HC_HCT125 v.3
Modifications:	• New general description.			
74HC_HCT125 v.3	20120827	Product data sheet	-	74HC_HCT125_CNV v.2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT125_CNV v.2	19970827	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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17. Contents

1 General description 1
2 Features and benefits 1
3 Ordering information 1
4 Functional diagram 2
5 Pinning information 2
5.1 Pinning 2
5.2 Pin description 3
6 Functional description 3
7 Limiting values 3
8 Recommended operating conditions 4
9 Static characteristics 4
10 Dynamic characteristics 6
11 Waveforms 7
12 Package outline 10
13 Abbreviations 14
14 Revision history 14
15 Legal information 15
15.1 Data sheet status 15
15.2 Definitions 15
15.3 Disclaimers 15
15.4 Trademarks 16
16 Contact information 16
17 Contents 17

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